Customer Training Workshop
Traveo™ II Nonvolatile Memory Programming

Q4 2020
## Target Products

### Target product list for this training material

<table>
<thead>
<tr>
<th>Family Category</th>
<th>Series</th>
<th>Code Flash Memory Size</th>
</tr>
</thead>
<tbody>
<tr>
<td>Traveo™ II Automotive Body Controller Entry</td>
<td>CYT2B6</td>
<td>Up to 576KB</td>
</tr>
<tr>
<td>Traveo II Automotive Body Controller Entry</td>
<td>CYT2B7</td>
<td>Up to 1088KB</td>
</tr>
<tr>
<td>Traveo II Automotive Body Controller Entry</td>
<td>CYT2B9</td>
<td>Up to 2112KB</td>
</tr>
<tr>
<td>Traveo II Automotive Body Controller Entry</td>
<td>CYT2BL</td>
<td>Up to 4160KB</td>
</tr>
<tr>
<td>Traveo II Automotive Body Controller High</td>
<td>CYT3BB/4BB</td>
<td>Up to 4160KB</td>
</tr>
<tr>
<td>Traveo II Automotive Body Controller High</td>
<td>CYT4BF</td>
<td>Up to 8384KB</td>
</tr>
<tr>
<td>Traveo II Automotive Cluster</td>
<td>CYT3DL</td>
<td>Up to 4160KB</td>
</tr>
<tr>
<td>Traveo II Automotive Cluster</td>
<td>CYT4DN</td>
<td>Up to 6336KB</td>
</tr>
</tbody>
</table>
Introduction to Traveo II Body Controller Entry

**System Resources**

**Power**
- Sleep Control
  - POR
  - BOD
  - DVDD
  - VDD
  - PWRSYS-H/T
  - LOO

**Clock**
- Clock Control
  - ARM
  - TEST
  - PLL
  - SWPLL

**Reset**
- Reset Control
  - WFI
  - Test
  - Test Mode Entry
  - Digital I/O
  - Analog I/O

**Power Modes**
- Active/Power
  - Low Power Active/Power
  - Deep Sleep
  - Hibernate

**CPU Subsystem**
- Arm Cortex-M4
  - 160 MHz
- SRAM
  - 256 KB
  - 128 KB Work Flash
- eCT Flash
  - 160 KB Code Flash + 128 KB Work Flash

**Peripheral Interconnect (MMIO, PPU)**
- Prog.
- Analog
- SAR ADC
  - 12-bit
- SARMUX
  - 64 ch

**I/O Subsystem**
- High-Speed I/O Matrix, Smart I/O, Boundary Scan
- 5x Smart I/O
- Up to 146x GPIO_STD, 4x GPIO_ENH

**System Interconnect (Multi Layer AHB, IPC, MPU/SMPU)**

**CPU Subsystem**
- CPU
- SCB
- I2C
- SPI
- UART

**Peripheral Interconnect (MMIO, PPU)**
- eCT Flash
- SRAM
- CRYPTO
- S/W
- SWJ/MTB/CTI
- MUL
- NVIC
- MPU

**Power**
- PWRSYS
- REF
- POR
- XRES
- LVD
- BOD
- OVD
- LDO
- REF
- PWRSYS
- REF

**System Resources**
- Power
  - POR
  - BOD
  - DVDD
  - VDD
  - PWRSYS-H/T
  - LOO

**Clock**
- Clock Control
  - ARM
  - TEST
  - PLL
  - SWPLL

**Reset**
- Reset Control
  - WFI
  - Test
  - Test Mode Entry
  - Digital I/O
  - Analog I/O

**Power Modes**
- Active/Power
  - Low Power Active/Power
  - Deep Sleep
  - Hibernate

**Hint Bar**
Review TRM chapter 33 for additional details
Introduction to Traveo II Body Controller High

- **CPU Subsystem**
  - Arm Cortex-M7 350 MHz
  - eCT Flash 8384KB Code flash + 256KB Work flash
  - SRAM0 512KB
  - SRAM1 256KB
  - SRAM2 256KB
  - Crypto AES, SHA, CRC, TRNG, RSA, ECC

- **System Interconnect** (Multi Layer AXI/AHB, IPC, MPU/SMPU)
  - 115x TCPWM (TIMER, CTR, QD, PWM)
  - 10x CANFD
  - 1x FLEXRAY
  - 10x SCB (I2C, SPI, UART, LIN)
  - 20x LIN/LIN
  - 3x AUDIOSS (I2S/TDM In/Out)
  - 3x AES/DES/SHA

- **Peripheral Interconnect** (MMIO, PPU)
  - SWJ/ETM/ITM/CTI
  - ROM 64KB
  - 1x SMIF

- **I/O Subsystem**
  - Up to 191 x GPIO_STD, 4x GPIO_ENH, 45x HSIO_STD
  - Smart I/O, Boundary Scan

- **Power**
  - DeepSleep, Hibernate

- **System Resources**
  - Power: DeepSleep
  - Sleep Control
  - POR, BOD, OVP, LVD
  - REF, PWRSTBY, LDO
  - Clock
  - Clock Control
  - 2xILO, WDT, IMD, ECO, PLL
  - 4xPLL
  - Reset Control
  - XRES
  - Test
  - TestMode Entry
  - Digital DFT
  - Analog DFT

- **Digital DFT**
  - CPU Subsystem
  - Analog DFT
  - System Interconnect (Multi Layer AXI/AHB, IPC, MPU/SMPU)
  - Peripheral Interconnect (MMIO, PPU)

- **Hint Bar**
  - Review TRM chapter 37 for additional details

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Introduction to Traveo II Cluster

CPU Subsystem
- Arm Cortex-M7
- 320 MHz
- eCT Flash
- 6336KB Code flash + 128KB Work flash
- SRAM0
- 256KB
- SRAM1
- 256KB
- SRAM2
- 128KB
- Crypto
- AES, SHA, CRC, TRNG, RSA, ECC

Peripheral Interconnect (Multi Layer AXI/AHB, IPC, MPU/SMPU)

High-Speed I/O Matrix, Smart I/O, Boundary Scan

System Resources
- Power
- Clock
- Reset
- Mux
- SWJ/ETM/ITM/CTI

Flash Controller
- 8KB $Prog.$

Analog
- SAR ADC (12-bit)

Audio DAC
- 11x SCB

CSS Subsystem
- I2C, SPI, UART, LIN

RTC
- 2xILO

SARMUX
- 48 ch

Crypto
- AES, SHA, CRC, TRNG, RSA, ECC

GFX Subsystem
- ARM Cortex-M0+
- 100 MHz

GFX Interconnect (AXI)

1x RGB/MIPI Input
2x RGB/LVDS Output
2x LIN/UART
2x CANFD
2x CAN
2x CANFD Interface
3x PCM
5x SG
2x I2S
2x TDM
2x Mixer

GFX Interconnect (Hyperbus, Single SPI, Dual SPI, Quad SPI, Octal SPI)

1x ETH
10/100/1000 Ethernet + AVB

Vector Core

Matrix

LDO

Power Modes
- Active/Deep
- Load/Power/Active/Idle
- STANDBY

I/O Subsystem
- GPIO
- PCLK
- 52x GPIO_STD, 8x GPIO_ENH, 28x GPIO
- 2x LIN, 2x TDM, 4x PCM, 2x Mixer
- Audio DAC
- 4x TDM

INTERRUPT

WCO

SRAM1
- 256KB

25256 KB SRAM1

Controller

ROM
- 64KB

VRAM
- 4096KB

1x PCIe

Peripheral Interconnect (MMIO, PPU)

- Prog. Analog
- SAM ADC (12-bit)

GFX Interconnect (AXI)

ITCM
- 64 KB

DTCM
- 64 KB

SWJ/ETM/ITM/CTI
- NVIC, MPU, AXI

Arm Cortex-M7
- 320 MHz
- FPU (SP/DP)
- D$ 16KB
- I$ 16KB

ITCM
- 64 KB

DTCM
- 64 KB

SWJ/ETM/ITM/CTI
- NVIC, MPU, AXI

Arm Cortex-M0+
- 100 MHz
- SRAM
- 256 KB
- SRAM
- 0.256 KB

ROM Controller

MUL, NVIC, MPU

Arm Cortex-M0+
- 100 MHz

SRAM Controller

ROM Controller

LPECO

1x Smart IO

5x GPIO STD 5x GPIO ENH 28x GPIO 2x LIN 2x TDM 4x PCM 5x SG 4x I2S 2x TDM

I/O Subsystem

SWJ/MTB/CTI

MUL, NVIC, MPU

Hint Bar

Review TRM chapter 39 for additional details
NVM Programming Overview

› NVM programming supports flash-specific operations including:
  – Erase, Program, NORMAL access restrictions in SFlash\(^1\), and storing public key

› CYT2B6/B7/B9/BL supports programming through the debug access port (DAP), Cortex-M4, and Cortex-M0+

› CYT3BB/4BB/4BF, CYT3DL/4DN supports programming through DAP, Cortex-M7, and Cortex-M0+

› eFuse memory
  – eFuse memory consists of a set of eFuse bits
  – Some eFuse bits store fixed device parameters, including factory trim settings, life-cycle stages, DAP security settings, and encryption keys
  – Limited set of eFuse bits are available for customer use

\(^1\) Supervisory flash

Hint Bar
Review TRM chapter 33 for CYT2B, chapter 37 for CYT3B/4B and chapter 39 for CYT3D/4D for additional details
eFuse Memory Overview

› eFuse bits can be programmed (or “blown”) in a manufacturing environment
  – eFuse bits cannot be programmed on the field
› Multiple eFuses can be read at the bit- or byte-level through an SROM call
  – An unblown eFuse reads as logic 0 and a blown eFuse reads as logic 1
  – There are no hardware connections from eFuse bits to elsewhere in the device
› There are 1024 eFuse bits, of which 192 are available for custom purposes
Flash Programming Operations for CYT2

- Flash programming operations are implemented as system calls
- System calls are executed inside Cortex-M0+ (CM0+) IRQ0
- System calls can be performed by CM0+, Cortex-M4, or DAP
  - Each has a reserved IPC structure through which it can request CM0+ to perform a system call

For User Programming
- System calls can be made from the CM0+ or CM4 at any point during code execution

For Debugger and Programmer
- When the debug interface is acquired, the boot ROM enters busy-wait loop and waits for commands issued by the DAP

Hint Bar
Review TRM chapter 33 for CYT2B, chapter 37 for CYT3B/4B and chapter 39 for CYT3D/4D for additional details
Flash Programming Operations for CYT3/CYT4

- Flash programming operations are implemented as system calls
- System calls are executed inside CM0+ IRQ0
- System calls can be performed by CM0+, CM7_0, CM7_1, or DAP
  - Each has a reserved IPC structure through which it can request CM0+ to perform a system call

For User Programming
- System calls can be made from the CM0+ or CM7_0 or CM7_1 at any point during code execution

For Debugger and Programmer
- When the debug interface is acquired, the boot ROM enters busy-wait loop and waits for commands issued by the DAP

All operations to flash memory are done through the CM0+ (whether from the DAP or from the CPU)
## SROM API Library (1/3)

<table>
<thead>
<tr>
<th>No.</th>
<th>System Call</th>
<th>Opcode</th>
<th>Description</th>
<th>Access Allowed</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td></td>
<td></td>
<td></td>
<td>Normal1</td>
</tr>
<tr>
<td>1</td>
<td>BlankCheck</td>
<td>0x2A</td>
<td>Performs blank check on the addressed Work Flash</td>
<td>CM0+, Main CPU², DAP</td>
</tr>
<tr>
<td>2</td>
<td>BlowFuseBit</td>
<td>0x01</td>
<td>Blows an eFuse bit</td>
<td>CM0+, Main CPU², DAP</td>
</tr>
<tr>
<td>3</td>
<td>Calibrate</td>
<td>0x13</td>
<td>Applies trims from eFuse and validates SFlash and then load the trims</td>
<td>CM0+, Main CPU², DAP</td>
</tr>
<tr>
<td>4</td>
<td>CheckFactoryHash</td>
<td>0x27</td>
<td>Generates the FACTORY_HASH as per TOC1 and compares with the FACTORY1_HASH fuses</td>
<td>CM0+, Main CPU², DAP</td>
</tr>
<tr>
<td>5</td>
<td>CheckFMStatus</td>
<td>0x07</td>
<td>Returns the status of the flash operation</td>
<td>CM0+, Main CPU², DAP</td>
</tr>
<tr>
<td>6</td>
<td>Checksum</td>
<td>0x0B</td>
<td>Calculates the checksum of a flash region</td>
<td>CM0+, Main CPU², DAP</td>
</tr>
<tr>
<td>7</td>
<td>Compute Basic Hash</td>
<td>0x0D</td>
<td>Computes the hash value of a flash region</td>
<td>CM0+, Main CPU², DAP</td>
</tr>
<tr>
<td>8</td>
<td>ConfigureFMInterrupt</td>
<td>0x08</td>
<td>Configures the flash macro interrupt</td>
<td>CM0+, Main CPU², DAP</td>
</tr>
<tr>
<td>9</td>
<td>Direct Execute³</td>
<td>0x0F</td>
<td>Directly executes code located at a configurable address</td>
<td>DAP</td>
</tr>
<tr>
<td>10</td>
<td>EraseAll</td>
<td>0x0A</td>
<td>Erases all flash</td>
<td>CM0+, Main CPU², DAP</td>
</tr>
</tbody>
</table>

1 Refer to TRM chapter 14 (Chip Operational Modes)  
2 The main CPU refers to CM4 or CM7 CPU in the MCU.  
3 Direct Execute is only for CYT2B7/B9  

**Hint Bar**

Review TRM chapter 33 for CYT2B, chapter 37 for CYT3B/4B and chapter 39 for CYT3D/4D for additional details.  
Refer to the Device Security training section for additional details about Normal/Secure/Dead for Access Allowed.
# SROM API Library (2/3)

<table>
<thead>
<tr>
<th>No.</th>
<th>System Call</th>
<th>Opcode</th>
<th>Description</th>
<th>Access Allowed</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td></td>
<td></td>
<td></td>
<td>Normal¹</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td></td>
<td>Secure</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td></td>
<td>Dead</td>
</tr>
<tr>
<td>11</td>
<td>EraseResume</td>
<td>0x23</td>
<td>Resumes a suspended erase operation</td>
<td>CM0+, Main CPU², DAP</td>
</tr>
<tr>
<td>12</td>
<td>EraseSector</td>
<td>0x14</td>
<td>Erases a flash sector</td>
<td>CM0+, Main CPU², DAP</td>
</tr>
<tr>
<td>13</td>
<td>EraseSuspend</td>
<td>0x22</td>
<td>Suspends an ongoing erase operation</td>
<td>CM0+, Main CPU², DAP</td>
</tr>
<tr>
<td>14</td>
<td>GenerateHash</td>
<td>0x1E</td>
<td>Returns the truncated SHA-256 of the Flash boot programmed in SFlash</td>
<td>CM0+, Main CPU², DAP</td>
</tr>
<tr>
<td>15</td>
<td>SwitchOverRegulators³</td>
<td>0x11</td>
<td>Switches between REGHC and linear regulators</td>
<td>CM0+</td>
</tr>
<tr>
<td>16</td>
<td>ConfigureRegulator⁴</td>
<td>0x15</td>
<td>Configures high-current regulator (REGHC) for devices that include REGHC, or PMIC for devices that use PMIC control without REGHC</td>
<td>CM0+</td>
</tr>
<tr>
<td>17</td>
<td>ProgramRow</td>
<td>0x06</td>
<td>Programs the addressed flash page</td>
<td>CM0+, Main CPU², DAP</td>
</tr>
<tr>
<td>18</td>
<td>ReadFuseByte</td>
<td>0x03</td>
<td>Reads addressed eFuse byte</td>
<td>CM0+, Main CPU², DAP</td>
</tr>
<tr>
<td>19</td>
<td>ReadFuseByteMargin</td>
<td>0x2B</td>
<td>Reads addressed eFuse byte marginally</td>
<td>CM0+, Main CPU², DAP</td>
</tr>
</tbody>
</table>

³ SwitchOverRegulators is only for CYT3/4
⁴ ConfigureRegulator is only for CYT3/4

¹ Refer to TRM chapter 14 (Chip Operational Modes)
² The main CPU refers to CM4 or CM7 CPU in the MCU.

Hint Bar

Review TRM chapter 33 for CYT2B, chapter 37 for CYT3B/4B and chapter 39 for CYT3D/4D for additional details.

Refer to the Device Security training section for additional details about Normal/Secure/Dead for Access Allowed.
## SROM API Library (3/3)

<table>
<thead>
<tr>
<th>No.</th>
<th>System Call</th>
<th>Opcode</th>
<th>Description</th>
<th>Access Allowed</th>
<th>Normal</th>
<th>Secure</th>
<th>Dead</th>
</tr>
</thead>
<tbody>
<tr>
<td>20</td>
<td>ReadSWPU</td>
<td>0x2C</td>
<td>Reads the identified SWPU from SRAM</td>
<td>CM0+, Main CPU², DAP</td>
<td>CM0+, Main CPU², DAP</td>
<td></td>
<td></td>
</tr>
<tr>
<td>21</td>
<td>ReadUniqueID</td>
<td>0x1F</td>
<td>Reads the unique ID of the die from flash</td>
<td>CM0+, Main CPU², DAP</td>
<td>CM0+, Main CPU², DAP</td>
<td></td>
<td></td>
</tr>
<tr>
<td>22</td>
<td>SetEnforcedApproval</td>
<td>0x2E</td>
<td>Sets the EnforcedApproval bit in SRAM</td>
<td>CM0+</td>
<td>CM0+</td>
<td>CM0+</td>
<td></td>
</tr>
<tr>
<td>23</td>
<td>SiliconID</td>
<td>0x00</td>
<td>Returns Family ID, Revision ID, Silicon ID, and protection state</td>
<td>CM0+, Main CPU², DAP</td>
<td>CM0+, Main CPU², DAP</td>
<td></td>
<td></td>
</tr>
<tr>
<td>24</td>
<td>SoftReset</td>
<td>0x1B</td>
<td>Provides system reset or Main CPU² only reset</td>
<td>CM0+, Main CPU², DAP</td>
<td>CM0+, Main CPU², DAP</td>
<td></td>
<td></td>
</tr>
<tr>
<td>25</td>
<td>TransitiontoRMA</td>
<td>0x28</td>
<td>Converts parts from SECURE to RMA life-cycle stage</td>
<td>CM0+, Main CPU², DAP</td>
<td>CM0+, Main CPU², DAP</td>
<td></td>
<td></td>
</tr>
<tr>
<td>26</td>
<td>TransitiontoSecure</td>
<td>0x2F</td>
<td>Converts parts to Secure life-cycle stage</td>
<td>CM0+, Main CPU², DAP</td>
<td>CM0+, Main CPU², DAP</td>
<td></td>
<td></td>
</tr>
<tr>
<td>27</td>
<td>WriteRow</td>
<td>0x05</td>
<td>Programs SFlash</td>
<td>CM0+, Main CPU², DAP</td>
<td>CM0+, Main CPU², DAP</td>
<td></td>
<td></td>
</tr>
<tr>
<td>28</td>
<td>WriteSWPU</td>
<td>0x2D</td>
<td>Updates the identified SWPU in SRAM</td>
<td>CM0+, Main CPU², DAP</td>
<td>CM0+, Main CPU², DAP</td>
<td></td>
<td></td>
</tr>
<tr>
<td>29</td>
<td>DebugPowerUpDown³</td>
<td>0x12</td>
<td>Enables/disables CM7 debugging</td>
<td>CM0+, DAP</td>
<td>CM0+, DAP</td>
<td></td>
<td></td>
</tr>
<tr>
<td>30</td>
<td>LoadRegulatorTrims⁴</td>
<td>0x16</td>
<td>Sets proper trims to PWR.TRIM_HT_PWRTRIM_SYS_CTL</td>
<td>CM0+</td>
<td>CM0+</td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

1 Refer to TRM chapter 14 (Chip Operational Modes)  
2 The main CPU refers to CM4 or CM7 CPU in the MCU.  
3 DebugPowerUpDown is only for CYT3/4  
4 LoadRegulatorTrims is only for CYT3/4

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**Hint Bar**

Review TRM chapter 33 for CYT2B, chapter 37 for CYT3B/4B and chapter 39 for CYT3D/4D for additional details.

Refer to the Device Security training section for additional details about Normal/Secure/Dead for Access Allowed.
## API Summary (1/4)

<table>
<thead>
<tr>
<th>No.</th>
<th>System Call</th>
<th>Summary</th>
</tr>
</thead>
<tbody>
<tr>
<td>1</td>
<td>BlankCheck</td>
<td>Performs blank check on the addressed Work Flash.</td>
</tr>
<tr>
<td>2</td>
<td>BlowFuseBit</td>
<td>Blows the addressed eFuse bit. The read value of a blown eFuse bit is ‘1’.</td>
</tr>
<tr>
<td>3</td>
<td>Calibrate</td>
<td>Applies trims from eFuse, validates SFlash, and then loads the trims. This API can be invoked before blowing the NORMAL fuse to check if the nonvolatile memory configurations are correct. If the hash fails then computed hash will be OR'd with STATUS_HASH_FAIL.</td>
</tr>
<tr>
<td>4</td>
<td>CheckFactoryHash</td>
<td>Generates FACTORY_HASH as per TOC1 and compares with the FACTORY1_HASH fuses.</td>
</tr>
<tr>
<td>5</td>
<td>CheckFMStatus</td>
<td>Returns the status of the flash operation.</td>
</tr>
<tr>
<td>6</td>
<td>Checksum</td>
<td>Reads either the whole flash or a row of flash, and returns the sum of each byte read.</td>
</tr>
<tr>
<td>7</td>
<td>ComputeBasicHash</td>
<td>Generates the hash of the flash region provided using the formula: $H(n+1) = (H(n)\times2+\text{Byte})%127$; where $H(0) = 0$. This function returns an invalid address status if called on an out-of-bound flash region.</td>
</tr>
<tr>
<td>8</td>
<td>ConfigureFMInterrupt</td>
<td>Configures the flash macro interrupt. The functionalities provided are: - Set interrupt mask, - Clear interrupt mask, - Clear interrupt.</td>
</tr>
<tr>
<td>9</td>
<td>DirectExecute</td>
<td>Directly executes code located at a configurable address. The API is allowed in VIRGIN state. In NORMAL, SECURE, and DEAD states, the API is allowed only if the corresponding DIRECT_EXECUTE_DISABLE bit (in SFlash1/eFuse) is 0².</td>
</tr>
</tbody>
</table>

¹ Supervisory flash.
² The ROM code copies the DAP attributes into CM0+ before executing the API. After API execution, CM0+ retains DAP’s PC and attribute. (Note that Direct Execute is only for CYT2B).
<table>
<thead>
<tr>
<th>No.</th>
<th>System Call</th>
<th>Summary</th>
</tr>
</thead>
<tbody>
<tr>
<td>10</td>
<td>EraseAll</td>
<td>Erases the entire flash macro that is specified. This API will erase only the Code Flash. The API returns a fail status if the user does not have write access to flash based on the SMPU settings.</td>
</tr>
<tr>
<td>11</td>
<td>EraseResume</td>
<td>Resumes a suspended erase operation.</td>
</tr>
<tr>
<td>12</td>
<td>EraseSector</td>
<td>Starts an erase operation on a specified sector and cannot be called on SFlash(^1).</td>
</tr>
<tr>
<td>13</td>
<td>EraseSuspend</td>
<td>Suspends an ongoing erase operation. Do not read from a suspended sector. The Program Row API function returns an error if invoked on the suspended sector.</td>
</tr>
<tr>
<td>14</td>
<td>GenerateHash</td>
<td>Returns the truncated SHA-256 of the flash boot programmed in SFlash and optionally includes the public key and other objects as indicated in the Table of Contents (TOC).</td>
</tr>
<tr>
<td></td>
<td></td>
<td>Gets the flash boot size from TOC.</td>
</tr>
<tr>
<td></td>
<td></td>
<td>Typically, this function will be called to check if the HASH blown into eFuse matches with what the ROM boot expects it to be.</td>
</tr>
<tr>
<td>15</td>
<td>SwitchOverRegulators</td>
<td>Switch between the high-current regulator (REGHC or PMIC without REGHC) required to run CM7 and the linear regulator (LDO). It should be called to switch from LDO to REGHC before enabling CM7. The Configure Regulator system call should be called before using this function.</td>
</tr>
<tr>
<td>16</td>
<td>ConfigureRegulator</td>
<td>Configure the high-current regulator (REGHC) for devices that include REGHC, or PMIC for devices that use PMIC control without REGHC. It should be called to configure the desired regulator only once before switching to the regulator using the Switch Over Regulators system call.</td>
</tr>
<tr>
<td>17</td>
<td>ProgramRow</td>
<td>Programs the addressed flash page (Code Flash, Work Flash, or User SFlash(^1)). The user must provide the data to be loaded and the flash address to be programmed. The flash page should be in the erased state. Any system call using Flash Programming cannot be aborted or cancelled.</td>
</tr>
</tbody>
</table>

\(^1\) Supervisory flash.
<table>
<thead>
<tr>
<th>No.</th>
<th>System Call</th>
<th>Summary</th>
</tr>
</thead>
<tbody>
<tr>
<td>18</td>
<td>ReadFuseByte</td>
<td>Returns the value of an eFuse. The read value of a blown eFuse bit is ‘1’ and that of an unblown eFuse bit is ‘0’. This API inherits the client protection context.</td>
</tr>
<tr>
<td>19</td>
<td>ReadFuseByteMargin</td>
<td>Returns the eFuse contents of the addressed byte read marginally. The read value of a blown eFuse bit is ‘1’ and that of an unblown eFuse bit is ‘0’. This API inherits the client’s protection context.</td>
</tr>
<tr>
<td>20</td>
<td>ReadSWPU</td>
<td>Reads the identified SWPU from SRAM. The PU ID is based on the storage of SWPU in SFlash. Only one contiguous SWPU will index in SFlash even though there are two physically separate storage areas.</td>
</tr>
<tr>
<td>21</td>
<td>ReadUniqueID</td>
<td>Returns the unique ID of the die from SFlash.</td>
</tr>
<tr>
<td>22</td>
<td>SetEnforcedApproval</td>
<td>Sets the EnforcedApproval bit in SRAM. EnforcedApproval bit is stored in PC1 private SRAM. If this bit is set, the API checks for a supervised marker.</td>
</tr>
<tr>
<td>23</td>
<td>SiliconID</td>
<td>Returns a 12-bit family ID, 16-bit silicon ID, 8-bit revision ID, and the current protection state.</td>
</tr>
<tr>
<td>24</td>
<td>SoftReset</td>
<td>Resets the system by setting the CM0+ AIRCR system reset bit. This will result in a system-wide reset except for debug logic. This API can also be used to selectively reset just the CM4/CM7_0/CM7_1 cores based on ‘type’ parameter. CM4/CM7_0/CM7_1 should be in DeepSleep mode when it resets selectively.</td>
</tr>
<tr>
<td>25</td>
<td>TransitiontoRMA</td>
<td>Converts parts from SECURE to RMA life-cycle stage.</td>
</tr>
</tbody>
</table>

1 Supervisory flash

**Hint Bar**

Review TRM chapter 33 for CYT2B, chapter 37 for CYT3B/4B, chapter 39 for CYT3D/4D, and System Calls for additional details
## API Summary (4/4)

<table>
<thead>
<tr>
<th>No.</th>
<th>System Call</th>
<th>Summary</th>
</tr>
</thead>
<tbody>
<tr>
<td>26</td>
<td>TransitionToSecure</td>
<td>Validates the FACTORY_HASH and programs SECURE_HASH, secure access restrictions, and dead access restrictions into eFuse. Programs secure or secure with debug fuse to transition to SECURE or SECURE with DEBUG life-cycle stage. Only allowed in NORMAL_PROVISIONED stage.</td>
</tr>
<tr>
<td>27</td>
<td>WriteRow</td>
<td>Programs flash. User must provide data to be loaded and flash address to be programmed. This API can be called only on SFlash(^1). Performs pre-program, erase, and then programs the flash page with contents provided in SRAM.</td>
</tr>
<tr>
<td>28</td>
<td>WriteSWPU</td>
<td>Updates the identified SWPU in SRAM if the client has appropriate access. The PU ID is based on the storage of SWPU in SFlash. Only one contiguous SWPU indexes in SFlash even though there are two physically separate storages.</td>
</tr>
<tr>
<td>29</td>
<td>DebugPowerUpDown</td>
<td>Used for handling the power transitions of CM7_0/1 power domains to properly connect/disconnect debug probe to/from the device.</td>
</tr>
<tr>
<td>30</td>
<td>LoadRegulatorTrims</td>
<td>Used to adapt the output voltage for internal regulators during handover.</td>
</tr>
<tr>
<td>31</td>
<td>OpenRMA</td>
<td>Enables full access to the device in the RMA life-cycle stage upon successful execution.</td>
</tr>
</tbody>
</table>

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\(^1\) Supervisory flash

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**Hint Bar**

Example of Flash Memory Operation with API (1/2)

› Use Case
  – Flash erase by CM4/CM7 master using the Erase All API
    – CM4/CM7 requests a system call to CM0+
    – API parameters are passed using IPC
    – Erase All API parameters are as follows

Master (CM4/7) Setting Parameters of Erase All API

<table>
<thead>
<tr>
<th>Address</th>
<th>Value to be Written</th>
<th>Description</th>
</tr>
</thead>
<tbody>
<tr>
<td>IPC_DATA0 Register</td>
<td></td>
<td></td>
</tr>
<tr>
<td>Bits [31:0] SRAM_SCRATCH_ADDR</td>
<td>SRAM address where the API parameters are stored. This must be a 32-bit aligned address</td>
<td></td>
</tr>
<tr>
<td>SRAM_SCRATCH_ADDR</td>
<td></td>
<td></td>
</tr>
<tr>
<td>Bits [31:24]</td>
<td>0xA</td>
<td>Erase All opcode</td>
</tr>
<tr>
<td>Bits [23:0]</td>
<td>0xXXXXXX</td>
<td>Not used</td>
</tr>
</tbody>
</table>

Return of API Execution Result from CM0+

<table>
<thead>
<tr>
<th>Address</th>
<th>Value to be Written</th>
<th>Description</th>
</tr>
</thead>
<tbody>
<tr>
<td>SRAM_SCRATCH_ADDR</td>
<td></td>
<td></td>
</tr>
<tr>
<td>Bits [31:28]</td>
<td>0xA = SUCCESS</td>
<td></td>
</tr>
<tr>
<td>Bits [27:0]</td>
<td>Error Code</td>
<td>A failure status is indicated by 0xF00000XX</td>
</tr>
</tbody>
</table>
Use Case:

API Operation (1/3)

› Steps to activate Erase All API flow
  – SRAM_SCRATCH_ADDR = 0x08010000\(^1\)
  – Erase All opcode = 0xA000000

1. Acquire a lock
2. Write the opcode of Erase All to SRAM_SCRATCH_ADDR
3. Write SRAM_SCRATCH_ADDR to DATA0
4. Generate notification event by writing to the IPC_NOTIFY register
5. Wait to be released by the IPC by polling the IPC_RELEASE register or RELEASE event

\(^1\) SRAM addresses for the CY2B7/B9 series.
Use Case:
API Operation (2/3)

Steps to execute API flow of Erase All API

- Execution of API is performed by CM0+
- SRAM_SCRATCH_ADDR area is used as Status code after reading opcode

1. Detect API notification event
2. Read SRAM_SCRATCH_ADDR (0x080100001) from DATA0
3. Read the opcode (0x0A000000) from SRAM_SCRATCH_ADDR (0x08010000)
4. If opcode is unknown, write the failure code to SRAM_SCRATCH_ADDR (0x08010000)
5. Write the progress code to SRAM_SCRATCH_ADDR (0x08010000)
6. Execute Erase All
7. If the result is fail, write the failure code to SRAM_SCRATCH_ADDR (0x08010000)
8. Write the success code to SRAM_SCRATCH_ADDR (0x08010000)
9. Generate a release event by writing to the IPC_RELEASE register

1 SRAM addresses for the CY2B7/B9 series.
Use Case:

API Operation (3/3)

› Closed API flow of Erase All-API
› SRAM_SCRATCH_ADDR = 0x08010000¹
  - Erase All opcode = 0xA000000
  - SRAM_SCRATCH_ADDR area is stored in Status code

1. Detect API release event
2. Read the Status from DATA0
3. If the status code is failure, transfer to Fail operation and end API
4. If the status code is success, the API ends normally

› Release event can also be reported as an interrupt

¹ SRAM addresses for the CY2B7/B9 series.
Example of Flash Memory Operation with API (2/2)

〉 Use Case
- Program operation by CM4/CM7 using the Program Row API
  - CM4/CM7 requests a system call to CM0+
  - API parameters are passed using IPC
  - Program Row API parameters are as follows
- The example shows write operation with 64-bit test data (0x55AA55AA x 2) into code flash

Master (CM4/CM7) Setting Parameters of Program Row API

<table>
<thead>
<tr>
<th>Address</th>
<th>Value to be Written</th>
<th>Description</th>
</tr>
</thead>
<tbody>
<tr>
<td>IPC_DATA0 Register</td>
<td></td>
<td></td>
</tr>
<tr>
<td>Bits [31:0]</td>
<td>SRAM_SCRATCH_ADDR</td>
<td>SRAM address where the API parameters are stored. This must be a 32-bit aligned address</td>
</tr>
<tr>
<td>SRAM_SCRATCH_ADDR</td>
<td></td>
<td></td>
</tr>
<tr>
<td>Bits [31:24]</td>
<td>0x06</td>
<td>Program Row opcode</td>
</tr>
<tr>
<td>Bits [7:0]</td>
<td>0xFFFF</td>
<td>Not used</td>
</tr>
</tbody>
</table>

Return of API Execution Result from CM0+

<table>
<thead>
<tr>
<th>Address</th>
<th>Value to be Written</th>
<th>Description</th>
</tr>
</thead>
<tbody>
<tr>
<td>SRAM_SCRATCH_ADDR</td>
<td></td>
<td></td>
</tr>
<tr>
<td>Bits [31:28]</td>
<td>0xA = SUCCESS/Program command ongoing in background0xF = ERROR</td>
<td></td>
</tr>
<tr>
<td>Bits [27:0]</td>
<td>Error Code</td>
<td>A failure status is indicated by 0xF00000XX</td>
</tr>
</tbody>
</table>
Steps to activate Program Row API flow

1. Acquire a lock
2. Write the opcode of Program row/Data size/Flash address/SRAM_SCRATCH_DATA_ADDR to SRAM_SCRATCH_ADDR
   Write the 32-bit data (0x55AA55AA) to data[0]
   Write the 32-bit data (0x55AA55AA) to data[1]
3. Write SRAM_SCRATCH_ADDR to DATA0
4. Generate notification event by writing to the IPC_NOTIFY register
5. Wait to be returned success status (0xA)

1 SRAM addresses for the CY2B7/B9 series.
Use Case:
API Operation (2/3)

Steps to execute Program Row API flow

- Execution of API is performed by CM0+
- SRAM_SCRATCH_ADDR area is used as status code after reading opcode

1. Detect API notification event
2. Read the SRAM_SCRACH_ADDR (0x08010000) from DATA0
3. Read the opcode (0x06000000) from SRAM_SCRATCH_ADDR (0x08010000)
4. If opcode is unknown, write the failure code to SRAM_SCRATCH_ADDR (0x08010000)
5. Execute Program Row
6. If the result is fail, write the failure code to SRAM_SCRATCH_ADDR (0x08010000)
7. Write the success code to SRAM_SCRATCH_ADDR (0x08010000)
8. Generate a release event by writing to the IPC_RELEASE register

\[1\] SRAM addresses for the CY2B7/B9 series.
Use Case:

API Operation (3/3)

Closed API flow of Program Row API

- SRAM_SCRATCH_ADDR = 0x08010000
- Program Row opcode = 0x06000000
- SRAM_SCRATCH_ADDR area is stored in Status code

1. Detect API release event
2. If the status code is failure, transfer to Fail operation and end API
3. If the status code is success, API ends normally

Release event can also be reported as an interrupt
Part of your life. Part of tomorrow.
## Revision History

<table>
<thead>
<tr>
<th>Revision</th>
<th>ECN</th>
<th>Submission Date</th>
<th>Description of Change</th>
</tr>
</thead>
<tbody>
<tr>
<td>**</td>
<td>6136844</td>
<td>04/17/2018</td>
<td>Initial release</td>
</tr>
<tr>
<td>*A</td>
<td>6409117</td>
<td>12/12/2018</td>
<td>Added the note descriptions. Added CYT2B9 and CYT4BF to Introduction. Updated the Block Diagram in Introduction, Flash Memory Operation with API table and API Summary table. Added eFuse section. Fixed the diagram of P17 (API Operation (2/3); IPC0 to IPC1).</td>
</tr>
<tr>
<td>*B</td>
<td>6639127</td>
<td>07/29/2019</td>
<td>Added CYT4DN to the introduction and added information in all sections. Updated page 2. Added Program Row API use case in Example of Flash Memory Operation with API in pages 20 to 23.</td>
</tr>
</tbody>
</table>